

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE30ND07S uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

V_{DS} =30V,I_D =7A

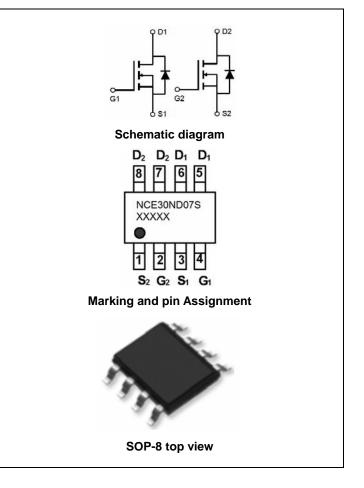
 $R_{DS(ON)}$ < 23m Ω @ V_{GS} =10V

 $R_{DS(ON)}$ < 40m Ω @ V_{GS} =4.5V

- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
30ND07S	NCE30ND07S	SOP-8	Ø330mm	12mm	4000 units

Absolute Maximum Ratings (T₄=25 °C unless otherwise noted)

Appendix maximum ratings (14-20 samess			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	7	Α
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	4.95	А
Pulsed Drain Current	I _{DM}	40	А
Maximum Power Dissipation	P _D	2	W
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	°C

Thermal Characteristic

Parameter	Symbol	Тур	Max	Unit
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	62.5	85	°C/W

NCE30ND07S

Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Off Characteristics							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	30	-	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V,V _{GS} =0V	-	-	1	μA	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA	
On Characteristics (Note 3)							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_{D}=250\mu A$	1.1	-	2.1	V	
Drain-Source On-State Resistance	Б	V _{GS} =10V, I _D =7A	-	18	23	mΩ	
	R _{DS(ON)}	V _{GS} =4.5V, I _D =6A	-	25	40		
Forward Transconductance	g FS	V_{DS} =5 V , I_D =7 A	-	15	-	S	
Dynamic Characteristics (Note4)	<u> </u>		•				
Input Capacitance	C _{lss}	\/ 45\/\/ 0\/	-	380	-	PF	
Output Capacitance	C _{oss}	V_{DS} =15V, V_{GS} =0V,	-	67	-	PF	
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	41	-	PF	
Switching Characteristics (Note 4)							
Turn-on Delay Time	t _{d(on)}		-	5	-	nS	
Turn-on Rise Time	t _r	V_{DD} =15V, R_L =2 Ω	-	3	-	nS	
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =3 Ω	-	15	-	nS	
Turn-Off Fall Time	t _f		-	3	-	nS	
Total Gate Charge	Qg	\/ -45\/ -74	-	7.2	-	nC	
Gate-Source Charge	Q _{gs}	V_{DS} =15V, I_{D} =7A, V_{GS} =4.5V	-	1.3	-	nC	
Gate-Drain Charge	Q_{gd}	V _{GS} =4.5V	-	1.7	-	nC	
Drain-Source Diode Characteristics	<u> </u>		•			-	
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =7A	-	-	1.2	V	
Diode Forward Current (Note 2)	I _S		-	-	7	Α	

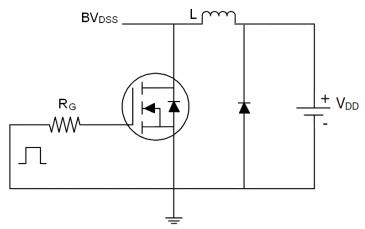
Notes:

- $\textbf{1.} \ \textbf{Repetitive Rating: Pulse width limited by maximum junction temperature}.$
- 2. The value of R _{8JA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T _A=25°C. The value in any given application depends on the user's specific board design. Surface Mounted on FR4 Board, t ≤ 10 sec. The current rating is based on the t ≤ 10s thermal resistance rating.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production.

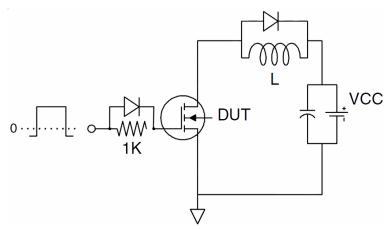


Test Circuit

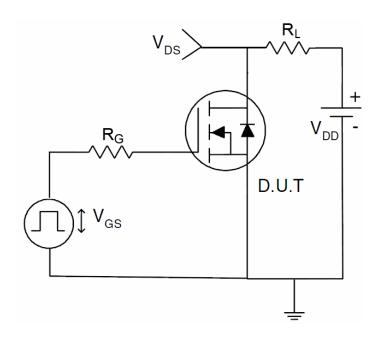
1) E_{AS} Test Circuits



2) Gate Charge Test Circuit:

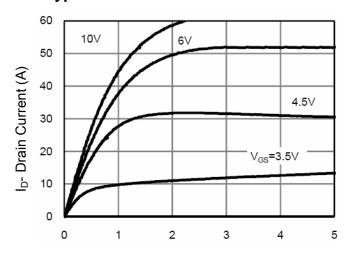


3) Switch Time Test Circuit:



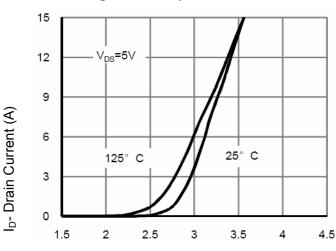


Typical Electrical and Thermal Characteristics (Curves)



Vds Drain-Source Voltage (V)

Figure 1 Output Characteristics



Vgs Gate-Source Voltage (V)
Figure 2 Transfer Characteristics

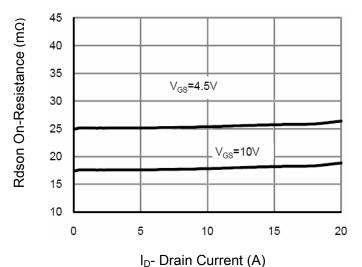


Figure 3 Rdson- Drain Current

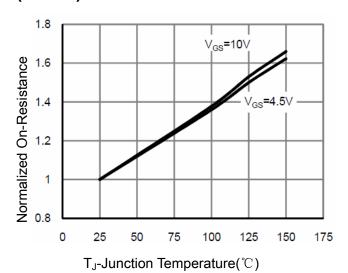
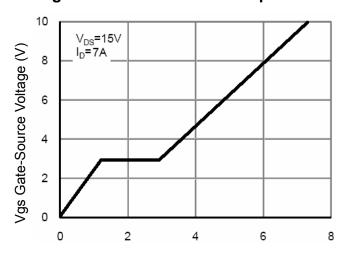
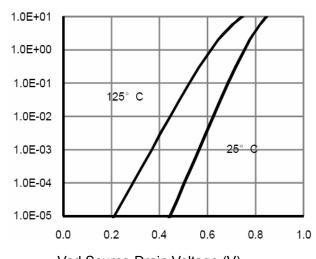


Figure 4 Rdson-JunctionTemperature



Qg Gate Charge (nC)
Figure 5 Gate Charge



Vsd Source-Drain Voltage (V)

Figure 6 Source- Drain Diode Forward



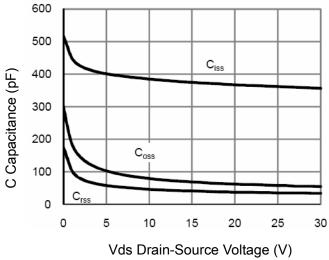


Figure 7 Capacitance vs Vds

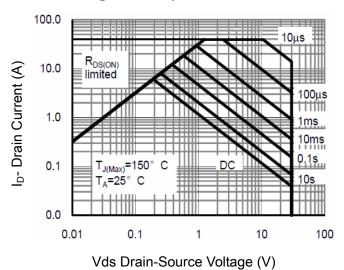
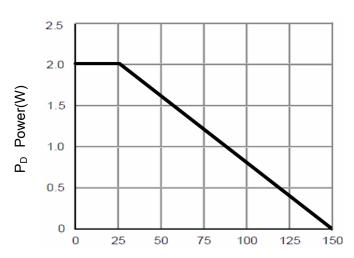


Figure 8 Safe Operation Area



 T_J -Junction Temperature(${}^{\circ}$ C) Figure 9 Power Dissipation



T_J-Junction Temperature(°C)

75

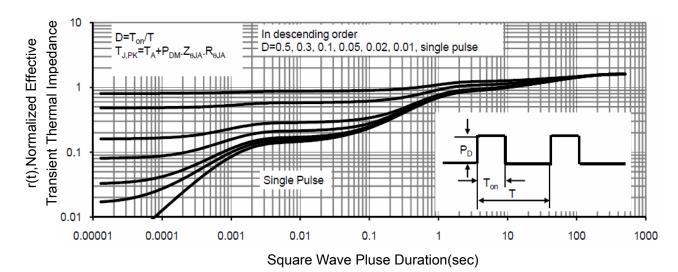
100

125

150

50

Figure 10 Current De-rating



0

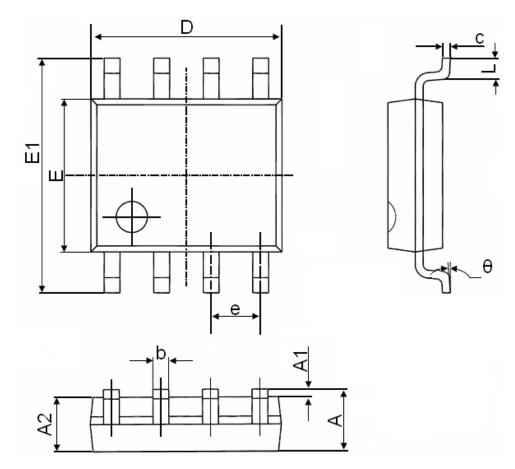
0

25

Figure 11 Normalized Maximum Transient Thermal Impedance

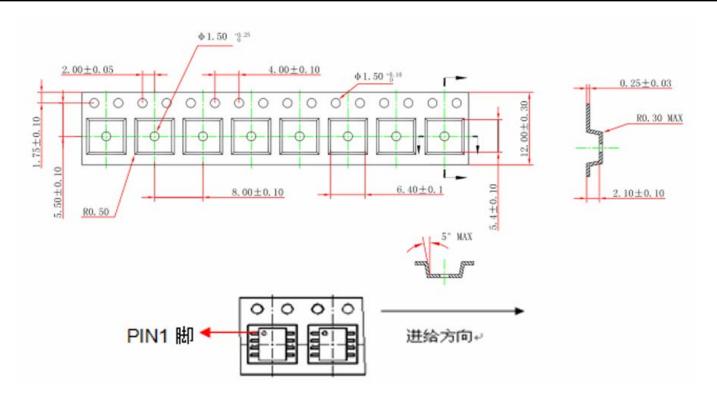


SOP-8 Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
Α	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
С	0.170	0.250	0.006	0.010	
D	4.700	5.100	0.185	0.200	
E	3.800	4.000	0.150	0.157	
E1	5.800	6.200	0.228	0.244	
е	1.270(BSC)		0.050	(BSC)	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	





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